

# WIDE BANDWIDTH **DUAL BIPOLAR OPERATIONAL AMPLIFIERS**

- INTERNALLY COMPENSATED
- SHORT-CIRCUIT PROTECTION
- GAIN AND PHASE MATCH BETWEEN **AMPLIFIER**
- LOW POWER CONSUMPTION
- PIN TO PIN COMPATIBLE WITH MC1458/LM358
- GAIN BANDWIDTH PRODUCT (at 100kHz) 5.5MHz

#### **DESCRIPTION**

The TJM4558 is a high performance monolithic dual operational amplifier.

The circuit combines all the outstanding features of the MC1458 and, in addition possesses three times the unity gain bandwidth of the industry standard.

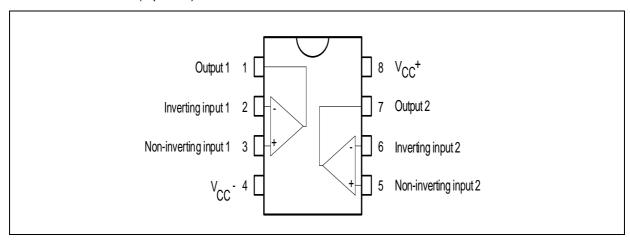
#### **ORDER CODE**

Part Number	Temperature	Package				
Fait Number	Range	N	D	Р		
TJM4558C	0°C, +70°C	•	•	•		
TJM45581	-40°C, +105°C	•	•	•		
Example: TJM4558CN						

N = Dual in Line Package (DIP)

# DIP8 (Plastic Package) **SO8** (Plastic Micropackage) TSSOP8 (Thin Shrink Small Outline Package)

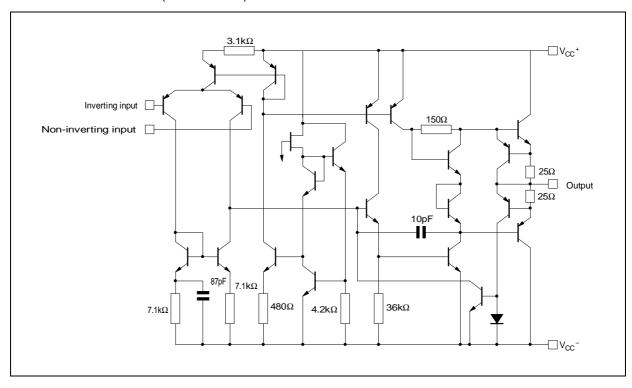
## PIN CONNECTIONS (top view)



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D = Small Outline Package (DIP)
D = Small Outline Package (SO) - also available in Tape & Reel (DT))
P = Thin Shrink Small Outline Package (TSSOP) - only available in Tape & Reel (PT)

# **SCHEMATIC DIAGRAM** (1/2 TJM4558)



## **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	TJM4558I	TJM4558C	Unit
V <sub>CC</sub>	Supply Voltage	±22		V
V <sub>i</sub>	Input Voltage	±	V	
V <sub>id</sub>	Differential Input Voltage	±;	V	
P <sub>tot</sub>	Power Dissipation	680		mW
	Output Short Circuit Duration	Infinite		
T <sub>oper</sub>	Operating Free-Air Temperature Range	-40 to +105 0 to +70		°C
T <sub>stg</sub>	Storage Temperature	remperature -65 to +150		°C

# **ELECTRICAL CHARACTERISTICS**

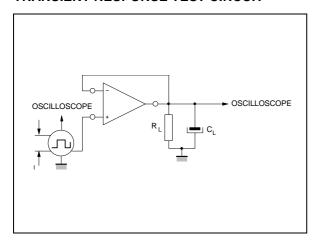
 $V_{CC} = \pm 15V$ ,  $T_{amb} = 25$ °C (unless otherwise specified)

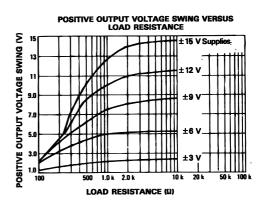
Symbol	Parameter	Min.	Тур.	Max.	Unit
	Input Offset Voltage ( $R_S \le 10k\Omega$ )				
$V_{io}$	$T_{amb} = +25$ °C		1	5	mV
	$T_{min} \le T_{amb} \le T_{max}$ .			6	
	Input Offset Current				
I <sub>io</sub>	$T_{amb} = +25$ °C		20	100	nA
	$T_{min} \le T_{amb} \le T_{max}$ .		40		
	Input Bias Current				
$I_{ib}$	$T_{amb} = +25$ °C		50	400	nA
	$T_{min} \le T_{amb} \le T_{max}$ .		100		
	Large Signal Voltage Gain ( $R_L = 2k\Omega$ , $V_0 = \pm 10V$ )		200		
$A_{vd}$	$T_{amb} = +25$ °C	50	200		V/mV
	$T_{min} \le T_{amb} \le T_{max}$	25			

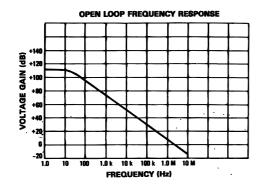
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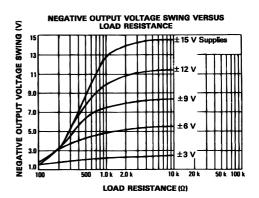
Symbol	Parameter	Min.	Тур.	Max.	Unit
	Supply Voltage Rejection Ratio $(R_s \le 10k\Omega)$				
SVR	$T_{amb} = +25$ °C		90		dB
	$T_{min} \le T_{amb} \le T_{max}$		77		
	Supply Current, all amplifiers, no load				
Icc	$T_{amb} = +25$ °C		2.3	4.5	mA
	$T_{min} \cdot \leq T_{amb} \leq T_{max}$ .		4		
	Input Common Mode Voltage Range				
V <sub>icm</sub>	$T_{amb} = +25$ °C	±12			V
	$T_{min} \le T_{amb} \le T_{max}$	±12			
	Common-mode Rejection Ratio $(R_s \le 10k\Omega)$				
CMR	$T_{amb} = +25^{\circ}C$		90		dB
	$T_{min} \le T_{amb} \le T_{max}$ .		70		
l <sub>os</sub>	Output Short Circuit Current	10	20		mA
	Output Voltage Swing				
.,	$T_{amb} = +25$ °C $R_L = 10k\Omega$	±12	±14		.,
V <sub>o</sub>	$R_L = 2k\Omega$	±10 ±12	±13		V
	$T_{min} \cdot \leq T_{amb} \leq T_{max}$ $R_L = 10k\Omega$ $R_L = 2k\Omega$	±12			
	Slew Rate				
SR	$(V_i = \pm 10, R_L = 2k\Omega, C_L = 100pF, T_{amb} = 25^{\circ}C, unity gain)$		2.2		V/µs
t <sub>r</sub>	Rise Time $(V_i = \pm 20\text{mV}, R_L = 2\text{k}\Omega, C_L = 100\text{pF}, T_{amb} = 25^{\circ}\text{C}, unity gain})$		0.3		μs
1/	Overshoot				0/
K <sub>OV</sub>	$(V_i = \pm 20 \text{mV}, R_L = 2 \text{k}\Omega, C_L = 100 \text{pF}, T_{amb} = 25 ^{\circ}\text{C}, \text{ unity gain})$		15		%
R <sub>i</sub>	Input Resistance	0.3	2		МΩ
C <sub>i</sub>	Input Capacitance		1.4		pF
R <sub>o</sub>	Output Resistance		75		Ω
В	Unity Gain Bandwidth		2.8		MHz
GBP	Gain Bandwidth Product				MHz
GDP	$(V_i = 10mV, R_L = 2k\Omega, C_L = 100pF, f = 100kHz, T_{amb} = 25^{\circ}C)$		5.5		IVII⊐∠
THD	Total Harmonic Distortion (f = 1kHz, $A_v = 20dB$ , $R_L = 2k\Omega$ , $V_o = 2V_{pp}$ , $C_L = 100pF$ , $T_{amb} = 25^{\circ}C$ )		0.008		%
	2				nV
e <sub>n</sub>	Equivalent Input Noise Voltage ( $R_S = 100\Omega$ , $f = 1kHz$ )		12		<del>∏</del> √Hz
$V_{O1}/V_{O2}$	Channel Separation		120		dB

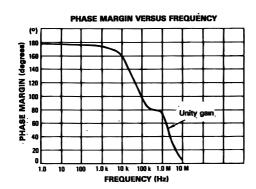
## TRANSIENT RESPONSE TEST CIRCUIT

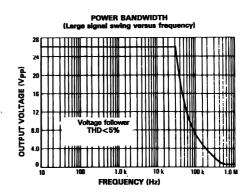










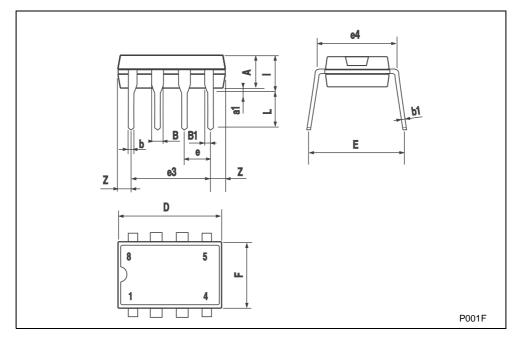


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# PACKAGE MECHANICAL DATA

# **Plastic DIP-8 MECHANICAL DATA**

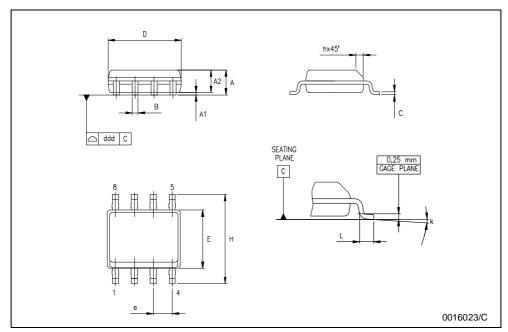
DIM	mm.			inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
Α		3.3			0.130		
a1	0.7			0.028			
В	1.39		1.65	0.055		0.065	
B1	0.91		1.04	0.036		0.041	
b		0.5			0.020		
b1	0.38		0.5	0.015		0.020	
D			9.8			0.386	
E		8.8			0.346		
е		2.54			0.100		
e3		7.62			0.300		
e4		7.62			0.300		
F			7.1			0.280	
I			4.8			0.189	
L		3.3			0.130		
Z	0.44		1.6	0.017		0.063	



# **PACKAGE MECHANICAL DATA**

## **SO-8 MECHANICAL DATA**

D114		mm.				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
А	1.35		1.75	0.053		0.069
A1	0.10		0.25	0.04		0.010
A2	1.10		1.65	0.043		0.065
В	0.33		0.51	0.013		0.020
С	0.19		0.25	0.007		0.010
D	4.80		5.00	0.189		0.197
E	3.80		4.00	0.150		0.157
е		1.27			0.050	
Н	5.80		6.20	0.228		0.244
h	0.25		0.50	0.010		0.020
L	0.40		1.27	0.016		0.050
k	8° (max.)					
ddd			0.1			0.04

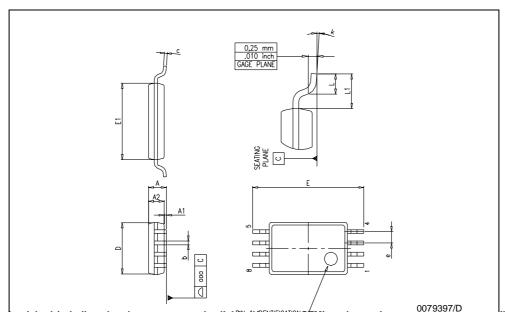


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#### **PACKAGE MECHANICAL DATA**

#### **TSSOP8 MECHANICAL DATA**

D.II.4	mm.			inch			
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.	
А			1.2			0.047	
A1	0.05		0.15	0.002		0.006	
A2	0.80	1.00	1.05	0.031	0.039	0.041	
b	0.19		0.30	0.007		0.012	
С	0.09		0.20	0.004		0.008	
D	2.90	3.00	3.10	0.114	0.118	0.122	
E	6.20	6.40	6.60	0.244	0.252	0.260	
E1	4.30	4.40	4.50	0.169	0.173	0.177	
е		0.65			0.0256		
К	0°		8°	0°		8°	
L	0.45	0.60	0.75	0.018	0.024	0.030	
L1		1			0.039		



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